

Thyristor Module

$$V_{RRM} = 2 \times 2200V$$

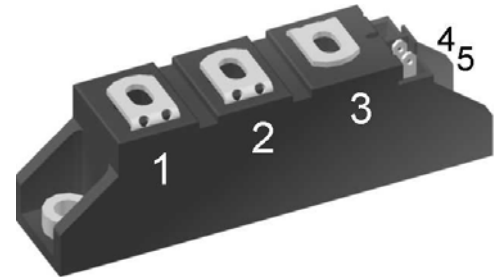
$$I_{TAV} = 104A$$

$$V_T = 1.46V$$


Phase leg

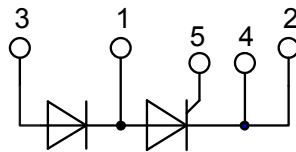
Part number

MCD94-22io1B



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

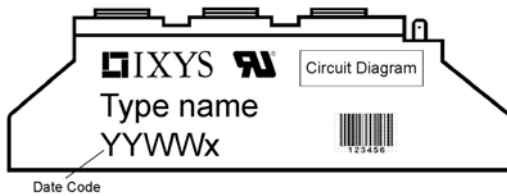
- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 3600V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Rectifier				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			2100	V	
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			2200	V	
I_{RD}	reverse current, drain current	$V_{RD} = 2200 V$	$T_{VJ} = 25^{\circ}C$		200	μA	
		$V_{RD} = 2200 V$	$T_{VJ} = 125^{\circ}C$		15	mA	
V_T	forward voltage drop	$I_T = 150 A$	$T_{VJ} = 25^{\circ}C$		1.44	V	
					1.74	V	
		$I_T = 300 A$	$T_{VJ} = 125^{\circ}C$		1.46	V	
					1.99	V	
I_{TAV}	average forward current	$T_C = 85^{\circ}C$	$T_{VJ} = 125^{\circ}C$		104	A	
$I_{T(RMS)}$	RMS forward current	180° sine			180	A	
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 125^{\circ}C$		0.85	V	
r_T	slope resistance				3.2	m Ω	
R_{thJC}	thermal resistance junction to case				0.22	K/W	
R_{thCH}	thermal resistance case to heatsink			0.20		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		455	W	
I_{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$		1.70	kA	
				$V_R = 0 V$		1.84	kA
		t = 8,3 ms; (60 Hz), sine	$T_{VJ} = 125^{\circ}C$			1.45	kA
				$V_R = 0 V$		1.56	kA
I^2t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			14.5	kA ² s
				$V_R = 0 V$		14.0	kA ² s
		t = 8,3 ms; (60 Hz), sine	$T_{VJ} = 125^{\circ}C$			10.4	kA ² s
				$V_R = 0 V$		10.1	kA ² s
C_J	junction capacitance	$V_R = 700 V$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$			63	pF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 125^{\circ}C$		10	W	
		$t_p = 300 \mu s$			5	W	
P_{GAV}	average gate power dissipation				0.5	W	
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^{\circ}C$; f = 50 Hz	repetitive, $I_T = 250 A$		150	A/ μs	
				$t_p = 200 \mu s$; $di_G/dt = 0.45 A/\mu s$;			
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}C$	non-repet., $I_T = 104 A$		500	A/ μs
					$R_{GK} = \infty$; method 1 (linear voltage rise)		1000
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		1.5	V	
			$T_{VJ} = -40^{\circ}C$		1.6	V	
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		150	mA	
			$T_{VJ} = -40^{\circ}C$		200	mA	
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}C$		0.25	V	
I_{GD}	gate non-trigger current				10	mA	
I_L	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		200	mA	
				$I_G = 0.45 A$; $di_G/dt = 0.45 A/\mu s$			
I_H	holding current	$V_D = 6 V$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		150	mA	
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs	
				$I_G = 0.45 A$; $di_G/dt = 0.45 A/\mu s$			
t_q	turn-off time	$V_R = 100 V$; $I_T = 150 A$; $V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}C$		185	μs	
		$di/dt = 10 A/\mu s$; $dv/dt = 20 V/\mu s$; $t_p = 200 \mu s$					

Package TO-240AA				Ratings		
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			200	A
T_{stg}	storage temperature		-40		125	°C
T_{VJ}	virtual junction temperature		-40		125	°C
Weight				90		g
M_D	mounting torque		2.5		4	Nm
M_T	terminal torque		2.5		4	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	13.0	9.7		mm
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm
V_{ISOL}	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V



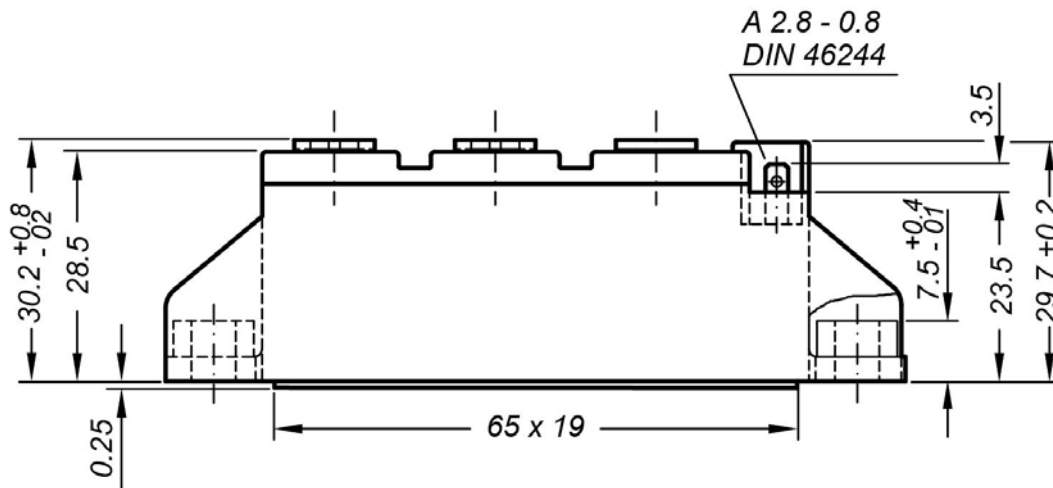
Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD94-22io1B	MCD94-22io1B	Box	6	470244

Equivalent Circuits for Simulation
** on die level*
 $T_{VJ} = 125\text{ °C}$

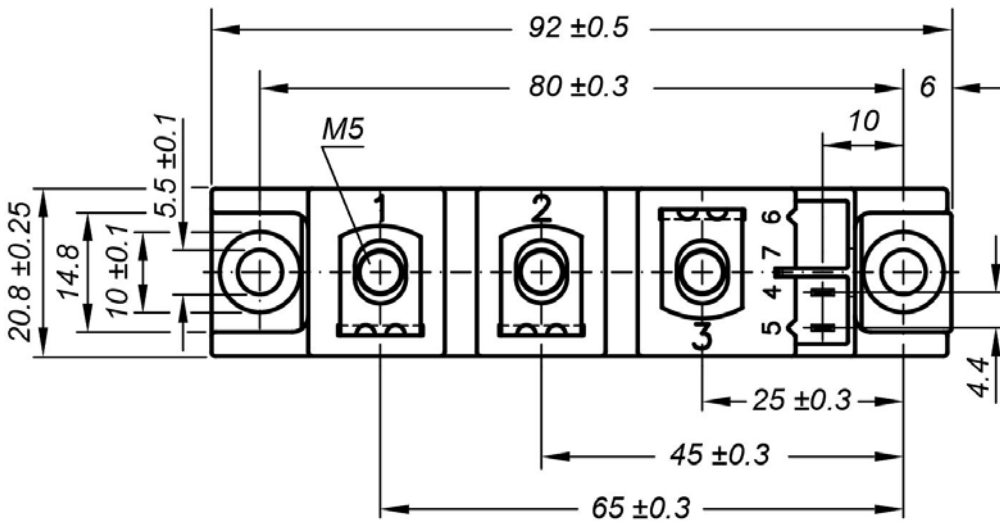
Thyristor

$V_{0\ max}$	threshold voltage	0.85	V
$R_{0\ max}$	slope resistance *	2	mΩ

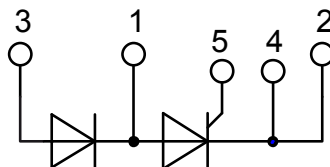
Outlines TO-240AA



General tolerance: DIN ISO 2768 class „c“



Optional accessories: Keyed gate/cathode twin plugs
Wire length: 350 mm, gate = white, cathode = red
UL 758, style 3751
Type **ZY 200L** (L = Left for pin pair 4/5)



Thyristor

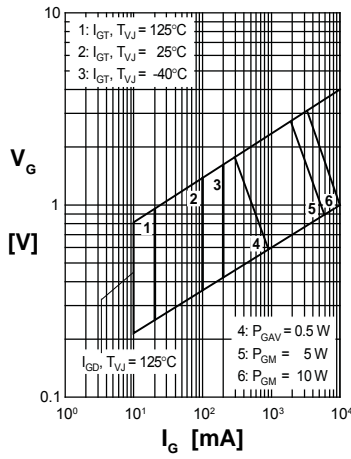


Fig. 1 Gate trigger characteristics

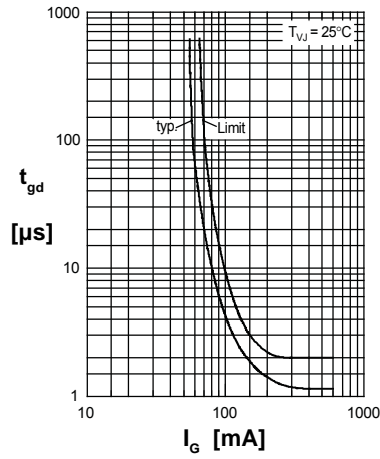


Fig. 2 Gate trigger delay time